Hex Buffer

The MC74LVX50 is an advanced high speed CMOS buffer fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 4.1 \text{ ns (Typ)}$ at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 3.6 V Operating Range
- Low Noise: $V_{OLP} = 0.5 \text{ V (Max)}$

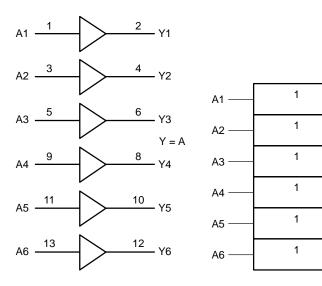


Figure 1. Logic Diagram

Figure 2. Logic Symbol

Y1

Y2

Y3

Y6



ON Semiconductor™

http://onsemi.com

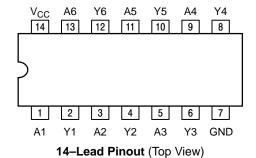




14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G



14-LEAD SOIC EIAJ M SUFFIX CASE 965



For detailed package marking information, see the Marking Diagram section on page 5 of this data sheet.

FUNCTION TABLE

A Input	Y Output
L	L
Н	Н

ORDERING INFORMATION

Device	Package	Shipping
MC74LVX50D	50D SO-14 55 Units	
MC74LVX50DT	TSSOP-14	96 Units/Rail
MC74LVX50M	SO EIAJ-14	50 Units/Rail

MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to $V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current	V _I < GND	-20	mA
lok	DC Output Diode Current	V _O < GND	±20	mA
l _{OUT}	DC Output Sink Current		± 25	mA
Icc	DC Supply Current per Supply Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case	e for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	(Note 1)		°C/W
		SOIC	125	
		TSSOP	170	
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL-94-VO (0.125 in)	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2)	> 2000	V
		Machine Model (Note 3)	> 200	
		Charged Device Model (Note 4)	2000	
I _{Latch-Up}	Latch-Up Performance	Above V _{CC} and Below GND at 85°C (Note 5)	±300	mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	Supply Voltage		2.0	3.6	V
VI	Input Voltage	(Note 6)	0	5.5	V
Vo	Output Voltage (HIC	GH or LOW State)	0	V _{CC}	V
T _A	Operating Free–Air Temperature		-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate Vo	$_{CC} = 3.0 \text{ V } \pm 0.3 \text{ V}$	0	100	ns/V

^{6.} Unused inputs may not be left open. All inputs must be tied to a high— or low–logic input voltage level.

NOTE: The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}		T _A = 25°(;	T _A ≤	85°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{IN} = V _{IH} or V _{IL})	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \mu A$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{IN} = V _{IH} or V _{IL})	$I_{OL} = 50 \mu A$ $I_{OL} = 50 \mu A$ $I_{OL} = 4 mA$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	3.6			2.0		20.0	μΑ

AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

					T _A = 25°C		$T_{A} \le 85^{\circ}C$		
Symbol	Parameter	Test Conditi	ions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, Input A to Y	V _{CC} = 2.7 V	$C_L = 15 pF$ $C_L = 50 pF$		5.4 7.9	10.1 13.6	1.0 1.0	12.5 16.0	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.1 6.6	6.2 9.7	1.0 1.0	7.5 11.5	
toshl	Output-to-Output Skew	V _{CC} = 2.7 V	C _L = 50 pF			1.5		1.5	ns
toslh	(Note 7)	V _{CC} = 3.3 V ±0.3V	C _L = 50 pF			1.5		1.5	
C _{IN}	Input Capacitance				4	10		10	pF

		Typical @ 25°C, V _{CC} = 3.3 V	
C_{PD}	Power Dissipation Capacitance (Note 8)	15	pF

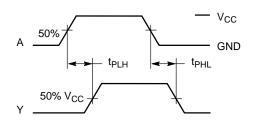
Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

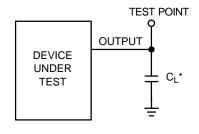
NOISE CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ns}$, $C_L = 50 \text{pF}$, $V_{CC} = 3.3 \text{ V}$

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

guaranteed by design.

8. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.





*Includes all probe and jig capacitance
Figure 4. Test Circuit

Figure 3. Switching Waveforms

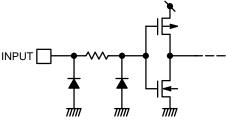
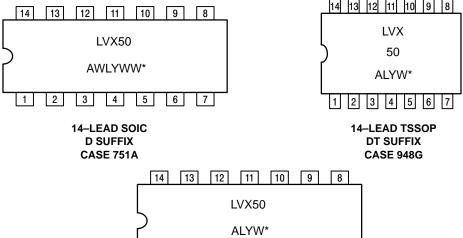


Figure 5. Input Equivalent Circuit

MARKING DIAGRAMS

(Top View) 14 13 12 11 10 9 8 LVX LVX50 50



14-LEAD SOIC EIAJ **M SUFFIX CASE 965**

4

5

6

3

| 1 |

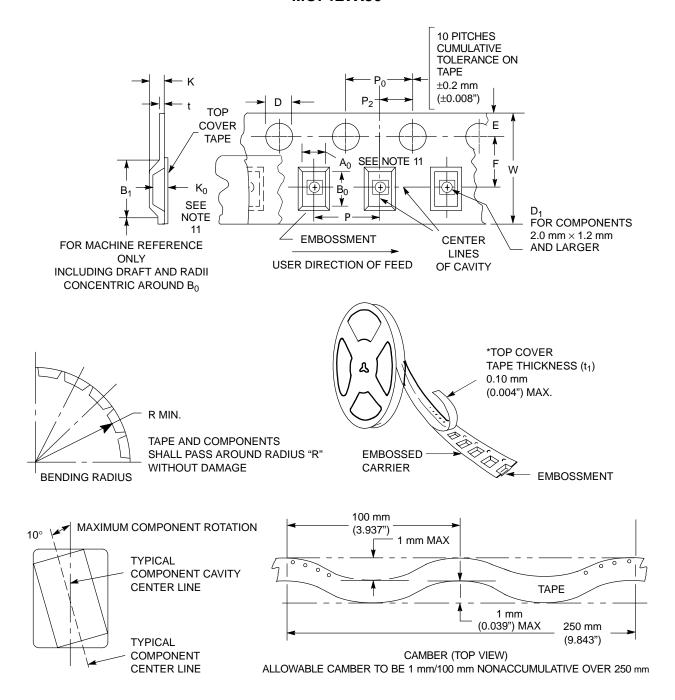
2

*See Applications Note #AND8004/D for date code and traceability information.

EMBOSSED CARRIER DIMENSIONS (See Notes 9 and 10)

Tape Size	B ₁ Max	D	D ₁	E	F	к	Р	P ₀	P ₂	R	Т	w
8 mm	4.35 mm (0.179")	1.5 mm + 0.1 -0.0 (0.059"	1.0 mm Min (0.179")	1.75 mm ±0.1 (0.069 ±0.004")	3.5 mm ±0.5 (1.38 ±0.002")	2.4 mm Max (0.094")	4.0 mm ±0.10 (0.157 ±0.004")	4.0 mm ±0.1 (0.157 ±0.004")	2.0 mm ±0.1 (0.079 ±0.004")	25 mm (0.98")	0.6 mm (0.024)	8.3 mm (0.327)
12 mm	8.2 mm (0.323")	+0.004 -0.0)	1.5 mm Min (0.060)		5.5 mm ±0.5 (0.217 ±0.002")	6.4 mm Max (0.252")	4.0 mm ±0.10 (0.157 ±0.004") 8.0 mm ±0.10 (0.315 ±0.004")			30 mm (1.18")		12.0 mm ±0.3 (0.470 ±0.012")
16 mm	12.1 mm (0.476")				7.5 mm ±0.10 (0.295 ±0.004")	7.9 mm Max (0.311")	4.0 mm ±0.10 (0.157 ±0.004") 8.0 mm ±0.10 (0.315 ±0.004") 12.0 mm ±0.10 (0.472 ±0.004")					16.3 mm (0.642)
24 mm	20.1 mm (0.791")				11.5 mm ±0.10 (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 mm ±0.10 (0.63 ±0.004")					24.3 mm (0.957)

Metric Dimensions Govern–English are in parentheses for reference only.
 A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity



11. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

Figure 6. Carrier Tape Specifications

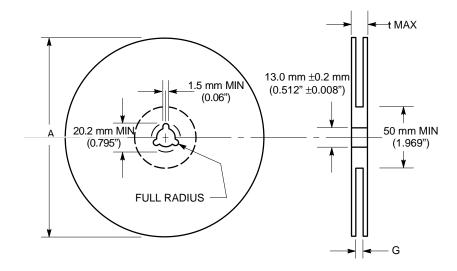


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
12 mm	R2	330 mm (13")	12.4 mm, +2.0 mm, -0.0 (0.49" + 0.079", -0.00)	18.4 mm (0.72")
16 mm	R2	360 mm (14.173")	16.4 mm, +2.0 mm, -0.0 (0.646" + 0.078", -0.00)	22.4 mm (0.882")
24 mm	R2	360 mm (14.173")	24.4 mm, +2.0 mm, -0.0 (0.961" + 0.078", -0.00)	30.4 mm (1.197")

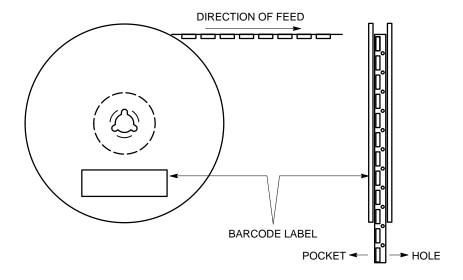


Figure 8. Reel Winding Direction

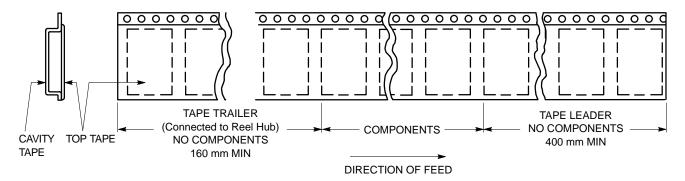


Figure 9. Tape Ends for Finished Goods

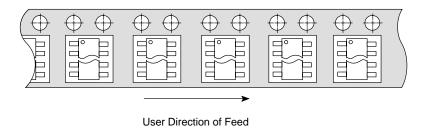


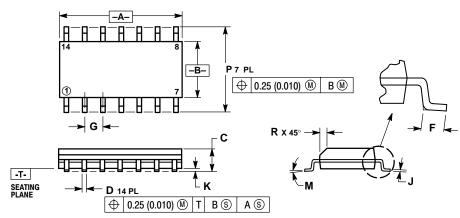
Figure 10. TSSOP and SOIC R2 Reel Configuration/Orientation

TAPE UTILIZATION BY PACKAGE

Tape Size	SOIC	TSSOP	QFN	SC88A / SOT-353 SC88/SOT-363
8 mm				5-, 6-Lead
12 mm	8-Lead	8-, 14-, 16-Lead	8-, 14-, 16-Lead	
16 mm	14-, 16-Lead	20-, 24-Lead	20-, 24-Lead	
24 mm	18-, 20-, 24-, 28-Lead	48-, 56-Lead	48-, 56-Lead	

PACKAGE DIMENSIONS

SO-14 **D SUFFIX** CASE 751A-03 ISSUE F

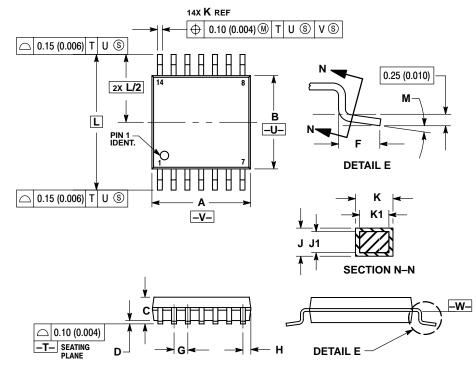


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP-14 **DT SUFFIX** CASE 948G-01 ISSUE O



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- Y 14.5M, 1982.

 CONTROLLING DIMENSION: MILLIMETER.

 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 DIMENSION B DOES NOT INCLUDE INTERLEAD
- FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED
- PHOI HUSION SHALL NOT EXCEED
 0.25 (0.10) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.03) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

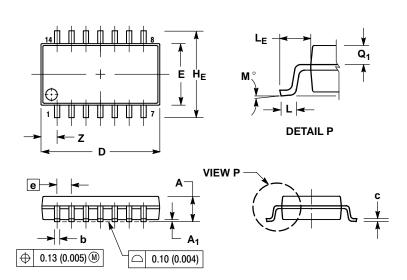
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

SO EIAJ-14 **M SUFFIX**

CASE 965-01 **ISSUE O**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1 42		0.056

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031

Phone: 81–3–5740–2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.